

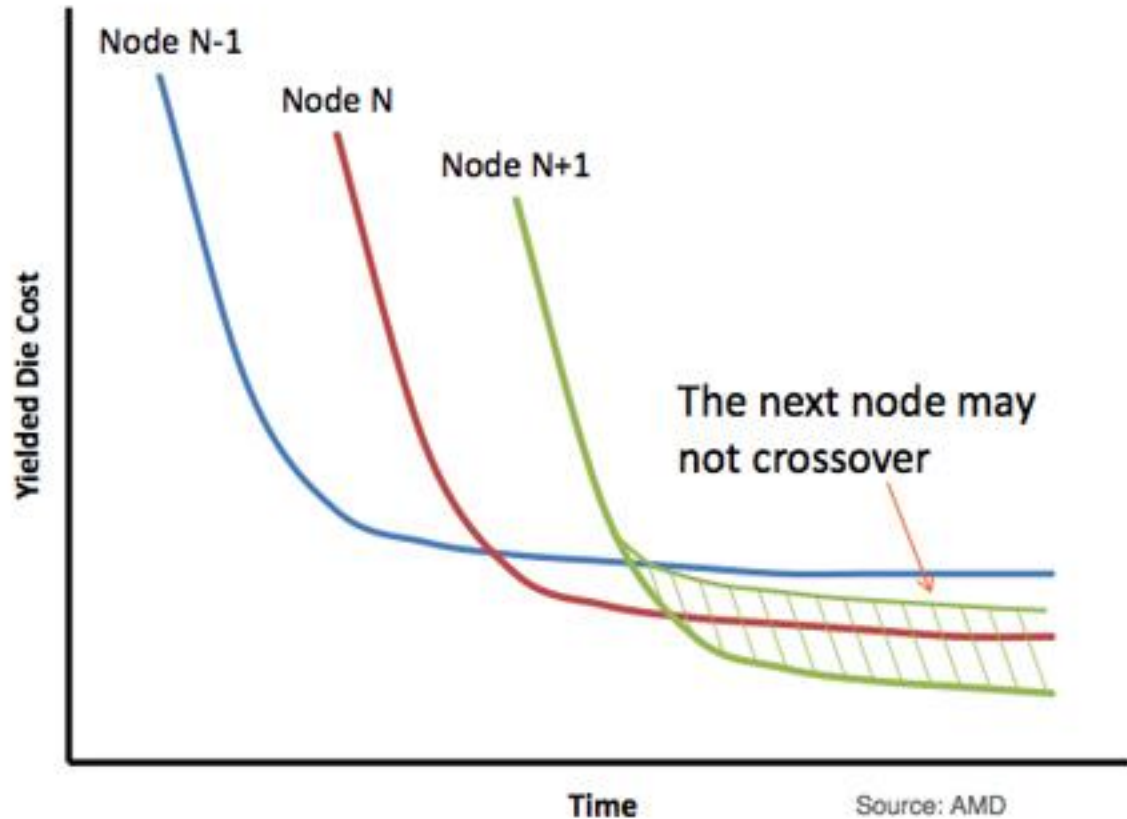


DiRAM™ Architecture Overview

David Chapman
VP Marketing

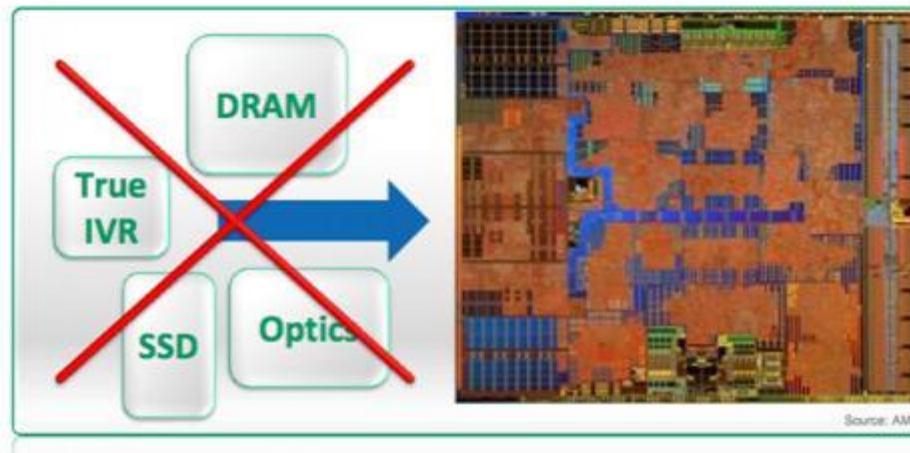


Why 3D? – Expiring Economics



AMD 2014 3D-ASIP

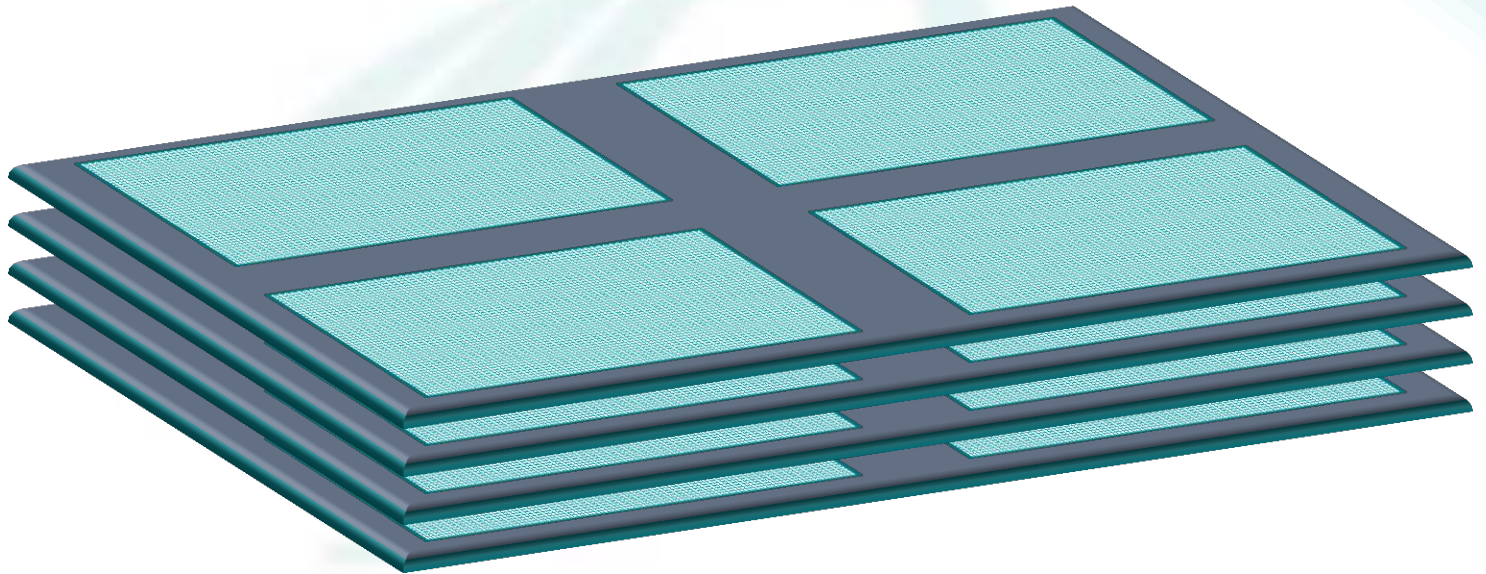
Why 3D? – Apples & Oranges



AMD 2014 3D-ASIP

Conventional 3D *Packaging*

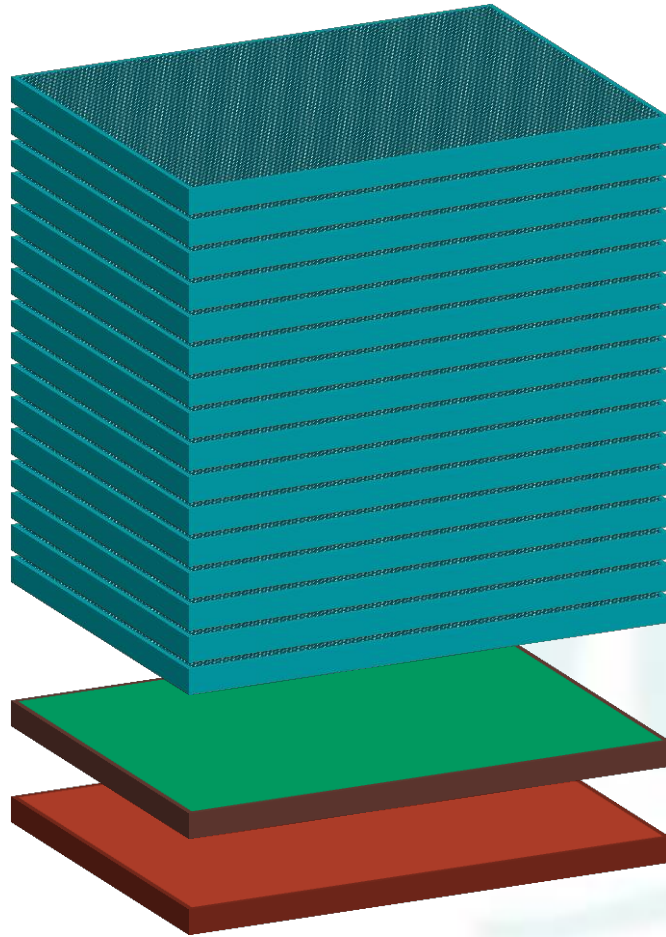
- Preserves traditional RAM problems
- Adds stacking costs



DiRAM™ True 3D RAM Architecture



Dis-Integrated 3D RAM Architecture



DiRAM™ Architecture

**Memory Cells
and
Access Transistors**

Sense Amps, etc.

I/O Layer

DiRAM4 Stack Internal Architecture

- **64 Gb** of Memory in 175 mm²
- **256** fully independent RAMs
- **16 Banks** per RAM
- **64 bit** Sep I/O Data per RAM
- **22ns tRC** (Page Open to Page Open in a Bank)
- **16 Tb/s Data Bandwidth @ Controller Layer**
- Competitive Manufacturing Cost

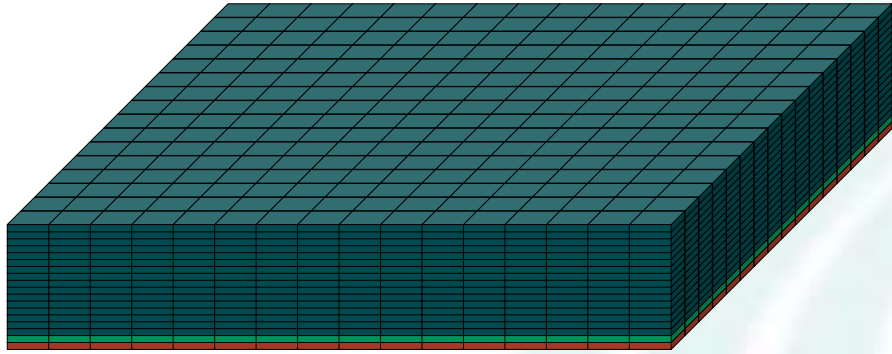
256 Independent RAMs

Each RAM



- 256 Mb Storage
- 64 Gb/s Bandwidth
- 9ns Latency
- 15ns tRC
- 16 Banks

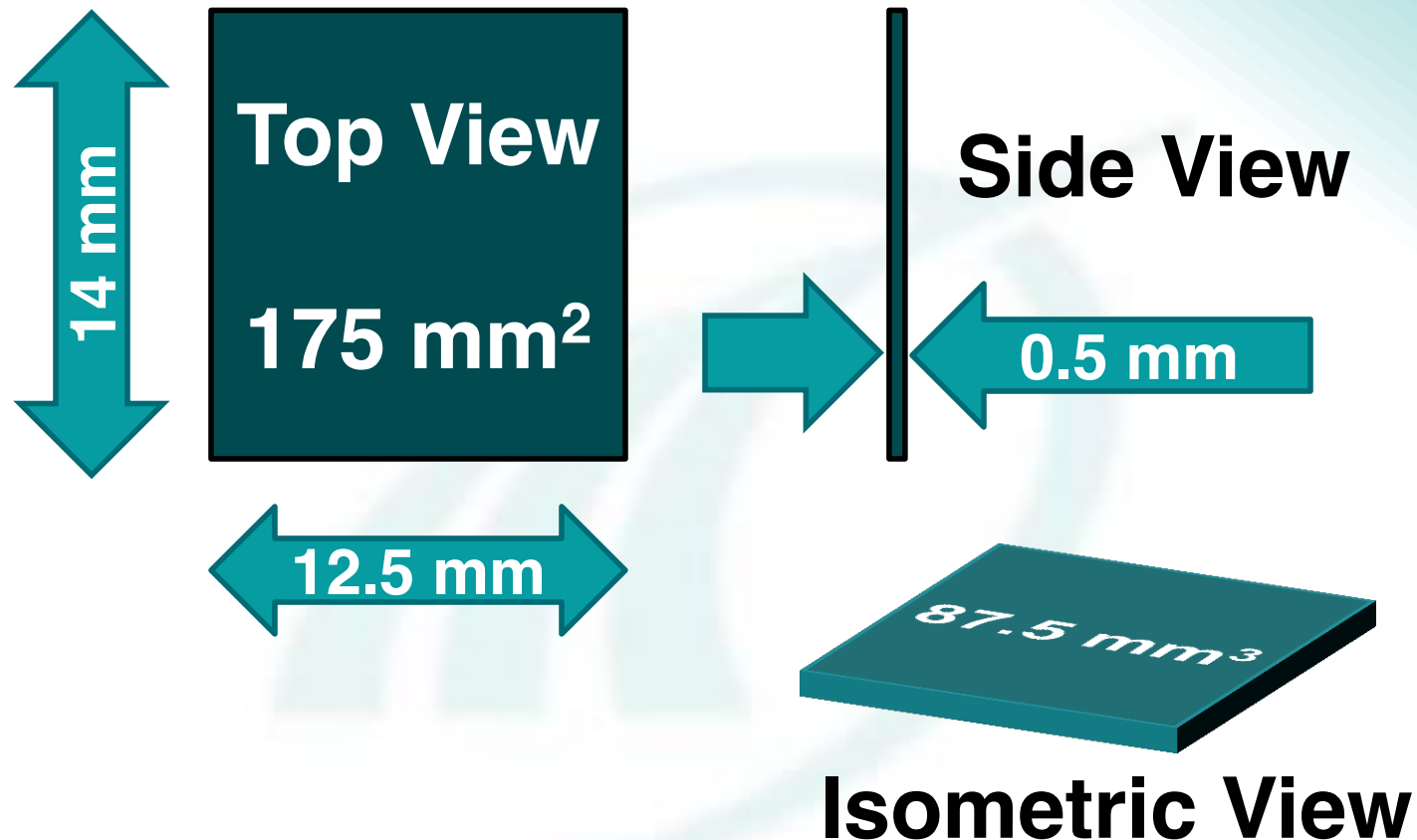
DiRAM4 64C64 Performance



**256
Independent
RAMs**

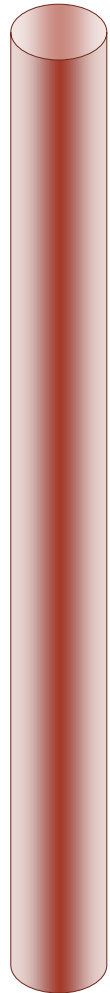
- **64 Gb** Storage
- 64 Ports
- 128 Channels
- **4096** Banks
- **> 4** Terabit/s Data Bandwidth
- 9 ns Latency
- **64 Billion** Transactions Per Second (Minimum)

DiRAM4 Scale* Drawing



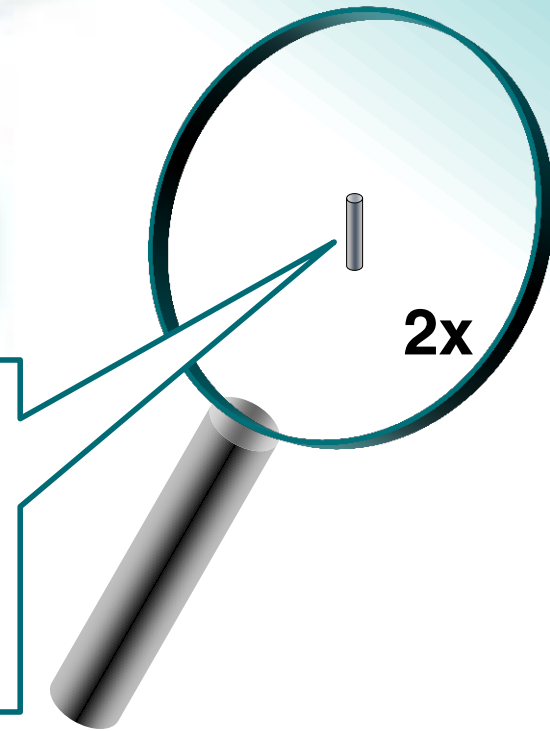
* Almost to scale

Via-Free Wafer Stacking



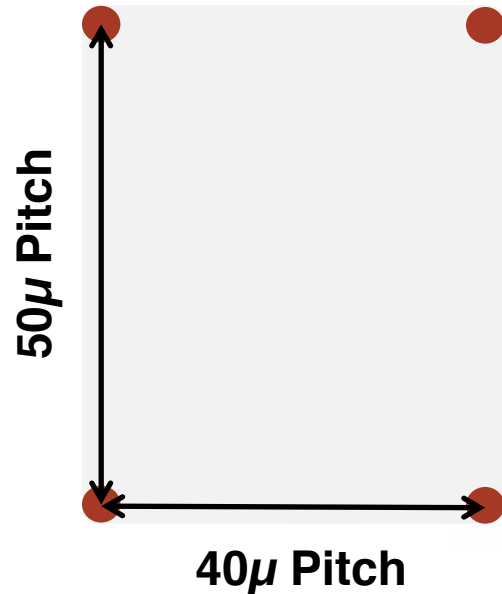
Aggressive
Copper TSV
 $\approx 5\mu \times 50\mu$

Tezzaron Tungsten
SuperContact™
 $<1\mu \times <10\mu$

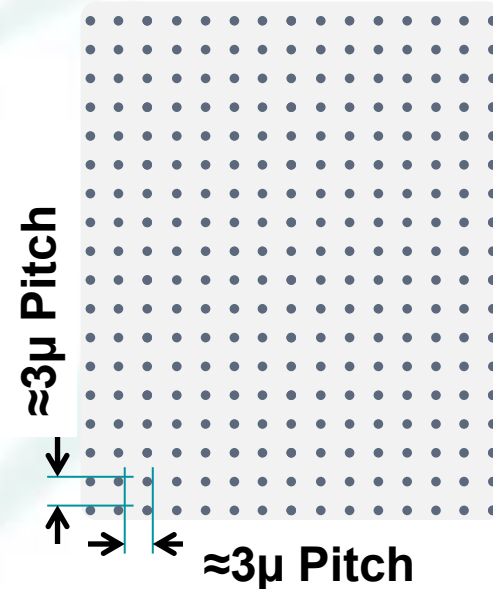


Common, Cheap, Fast and...Dense

**5 μ Diameter
Copper TSVs
(Stress driven Pitch)**



**<1 μ Diameter
Tungsten SuperContacts
(Alignment driven Pitch)**



Tezzaron wins: >66 to 1

Radically Different Manufacturing

Conventional Flow

- Fabricate Wafer
- Probe Test Die
- Thin Wafer
- Singulate Die
- Stack Good Die
- Package Stack
- Burn-In & Test Stack

Tezzaron Flow

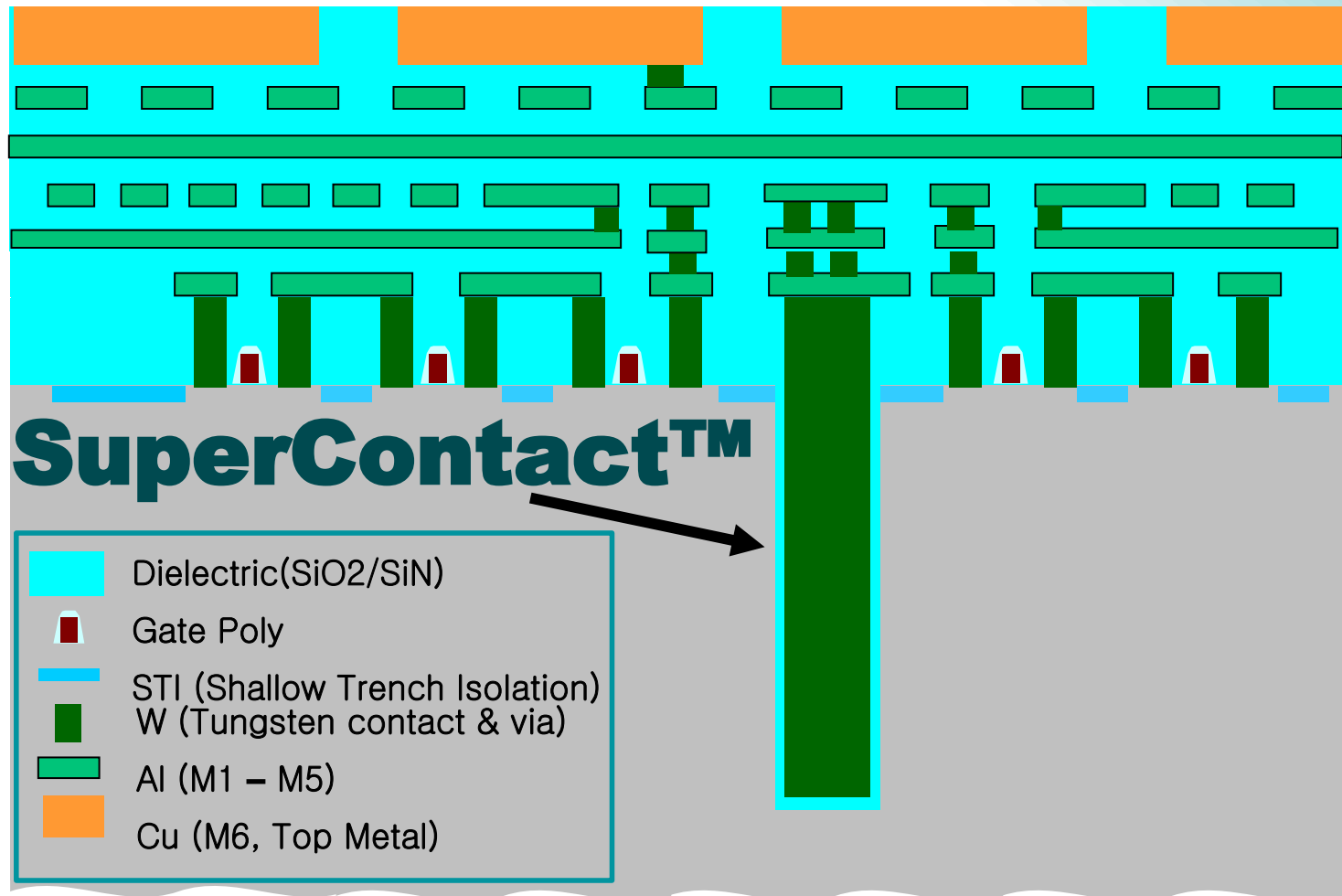
- Fabricate Wafer
- **Stack Wafers**
- **Thin Top Wafer**
- ***Repeat***
- **Probe Test Stacks**
- **Singulate Stacks**
- Package Stacks
- Burn-In & Test Stack

Never Handle A Thin Wafer

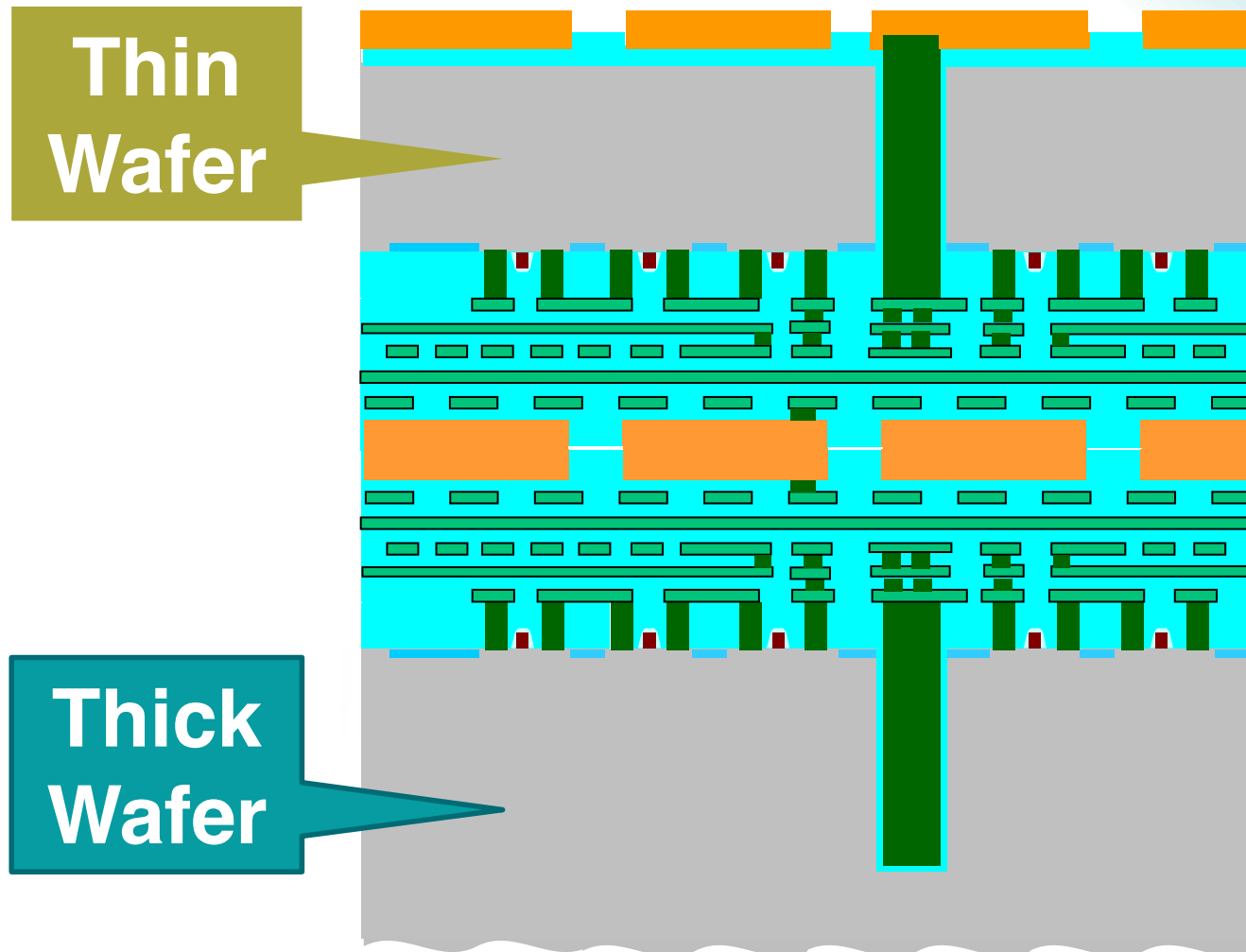
The Tezzaron Mantra

Bond Two...Grind One
...to make the world's
thinnest RAM wafers

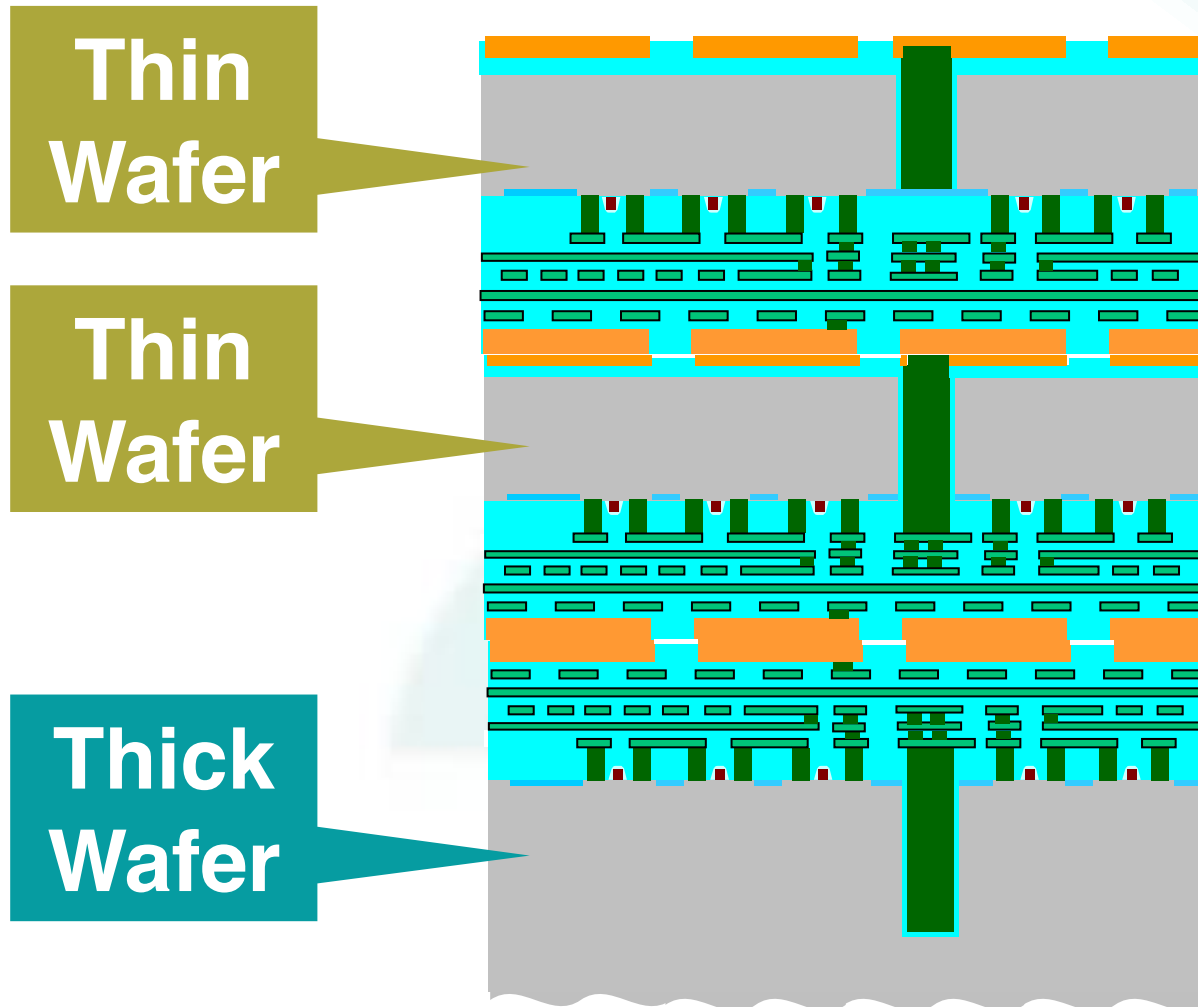
Step 1 – Build, Drill, Fill & Metalize



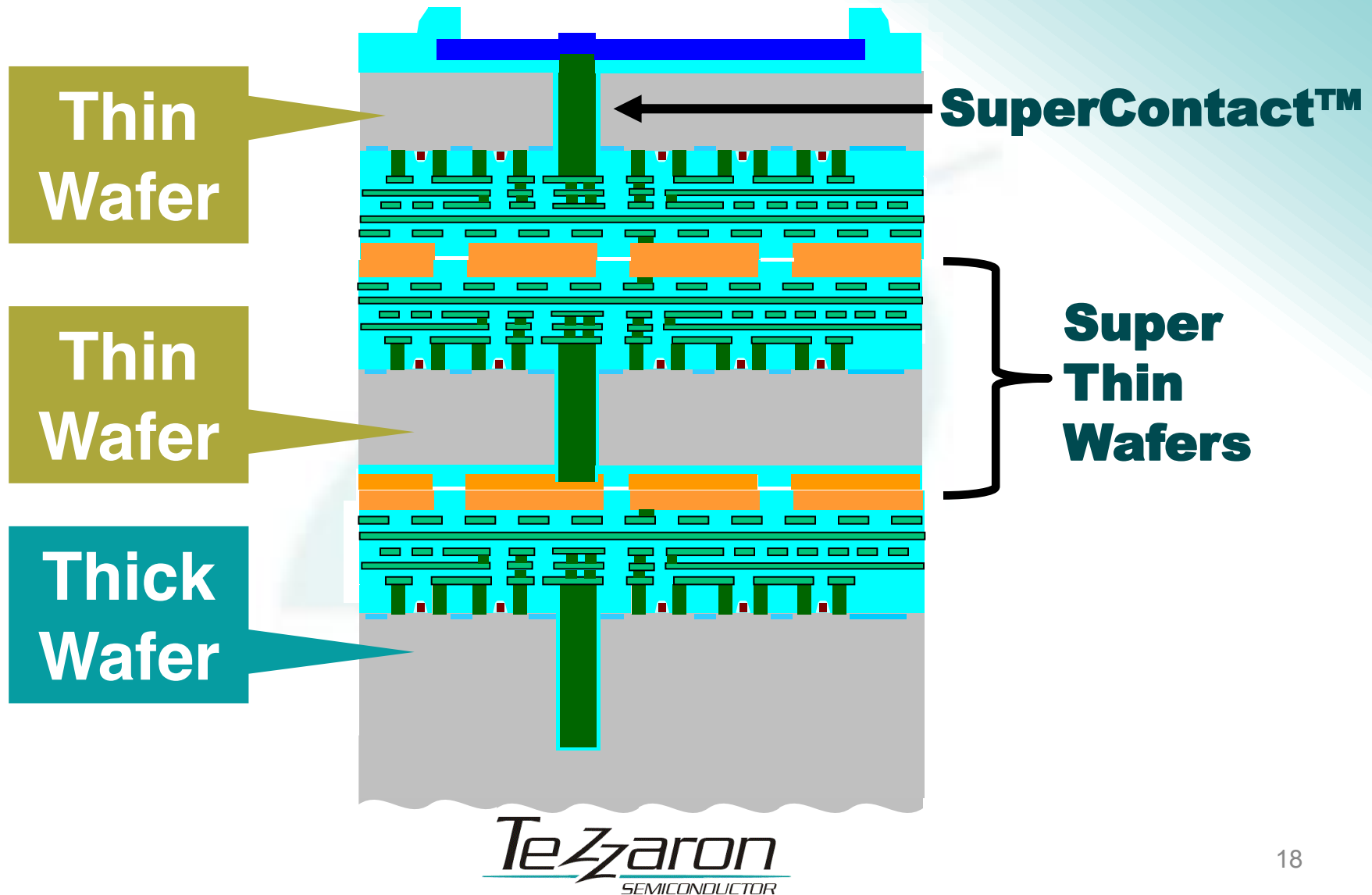
Step 2 – Bond, Thin & Re-metal



Step ($n-1$) – Rinse and Repeat



Step n – Build I/O Pads



“That can’t work...”

**“...bonding un-tested die will
produce near zero yields, poor
reliability and high costs.”**

Translation

You Tezzaron people are crazy!

Super dense interconnect allows...

Bi-STAR[®]

Built-in Self Test And Repair

- Controlled by **embedded ARM processor**
- Enabled by **per-cell** control interconnect
- Super-fine grained test and repair
- Continuous, in-the-system hard and soft error repair

Bi-STAR™ Does More, Works Better

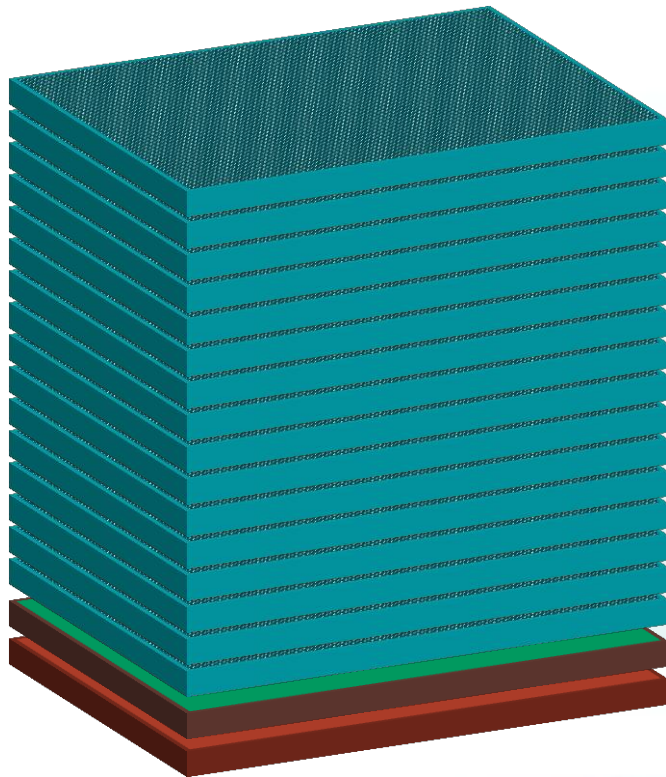
Bi-STAR Repairs

- Bad memory cells
- Bad line drivers
- Bad sense amps
- Shorted word lines
- Shorted bit-lines
- Leaky bits
- Bad secondary bus drivers

Bi-STAR Tests

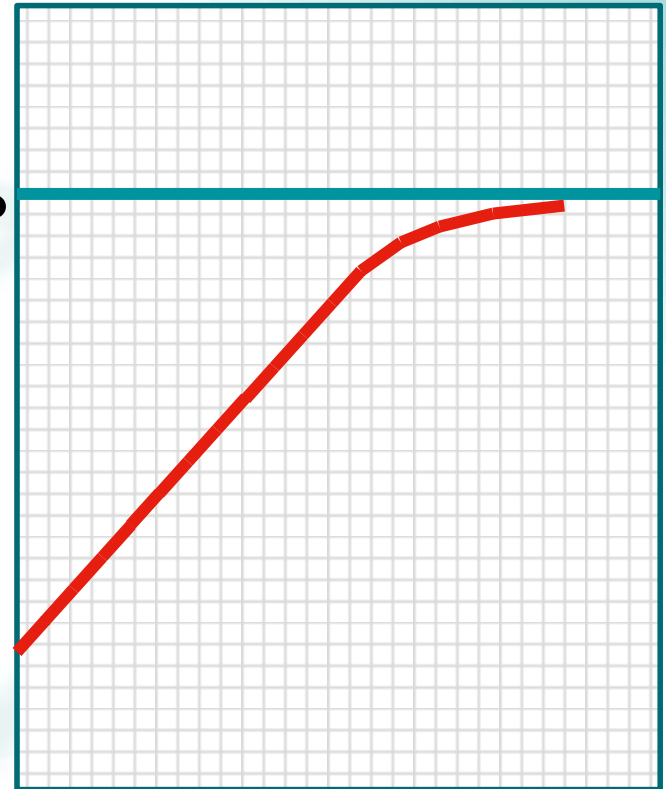
- Tests > 300,000 nodes per clock cycle
- Tests > 1,000x faster than external memory tester
- Via SPI port, works with Host to allow continuous scrub / repair

Bi-STAR Repair Improves Yield



100%

Yield



Stack Height

Solve 3D Problems with 3D

**Bonding
Untested
Wafers**

**Enables
Super Thin
Wafers**

**Enables
Effective
Repair**

**Enables
Tiny
Vias**



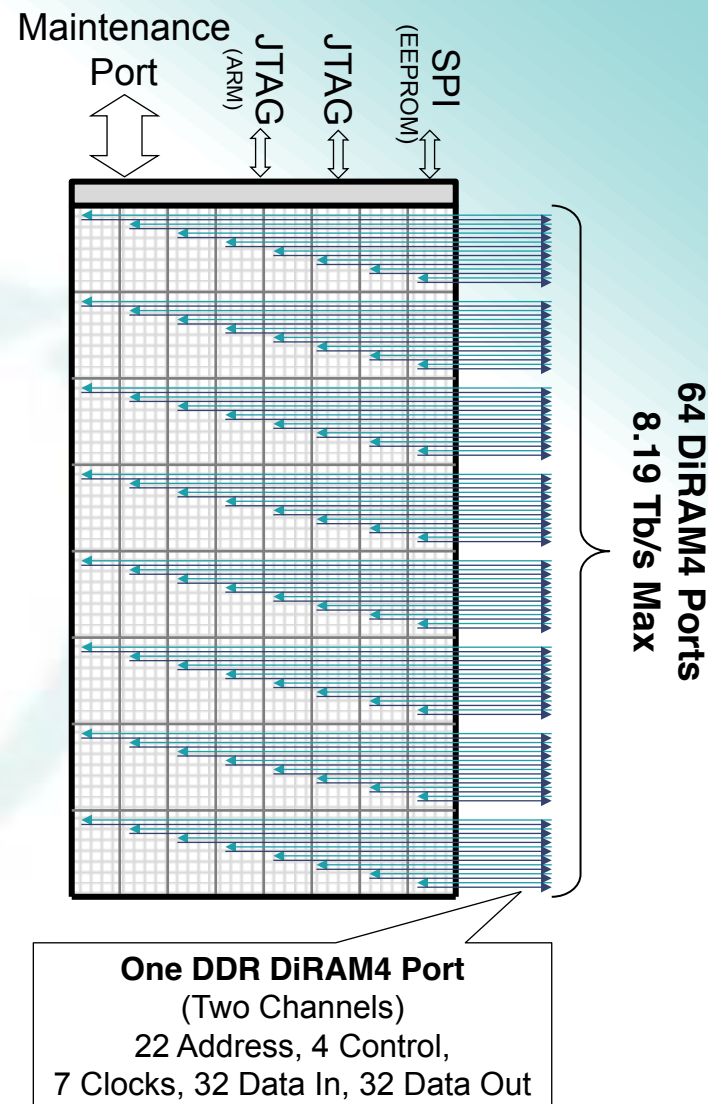
DiRAM: Efficiency for the Future

- **Less aggressive wafers**
- **Higher array efficiency**
- **Much lower test cost**
- **Higher yield**
- **Longer product life cycles**

64C64 Density and Performance

- **64 Gb** in 175 mm² footprint
- **64 Ports**
- **128 Channels**
- **32 Banks** per Channel
- **32 bit** Sep I/O per Port
- **14 ns** Worst Case Latency
- **22 ns** tRC
- **4 Tb/s** Min Data Bandwidth

(Page Open to Page Open in same Bank)



RAM is now Singular

DiRAM4™ Changes the Language of System Design...

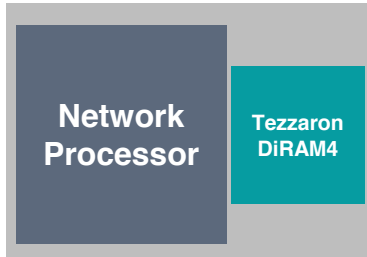
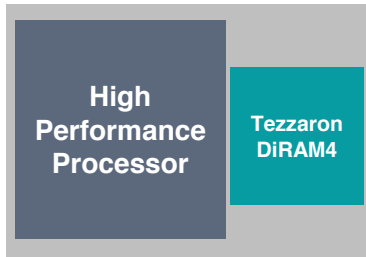


Table Memory + Packet Buffer

DiRAM4™ in Networking

- High Transaction Rate
- High Bandwidth
- High Density



Local Memory and/or Cache

DiRAM4™ in Computing

- High Bandwidth
- High Density
- Small References



Fast Local Memory

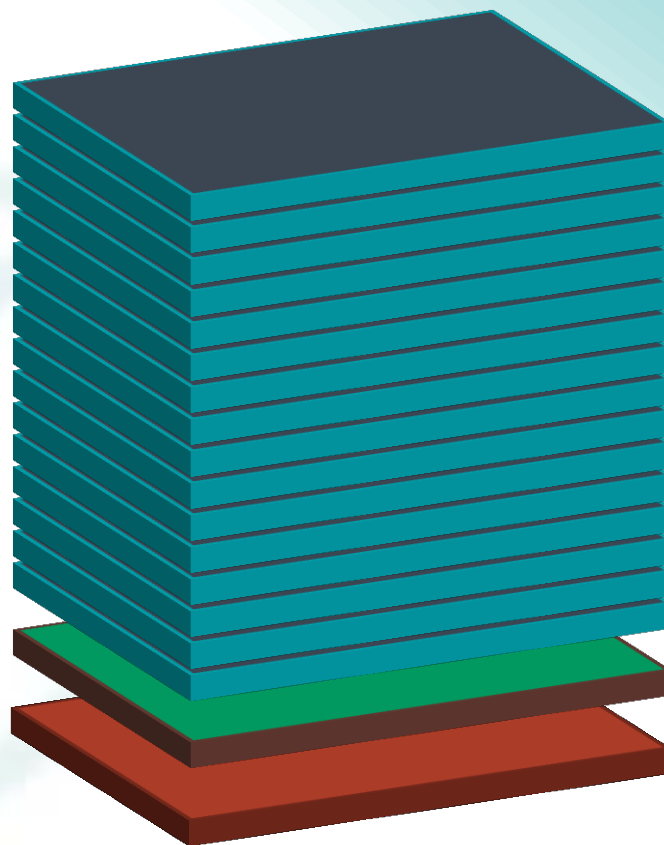
DiRAM4™ in Everything

- Multiple Independent Channels
- High Bandwidth
- High Transaction Rate

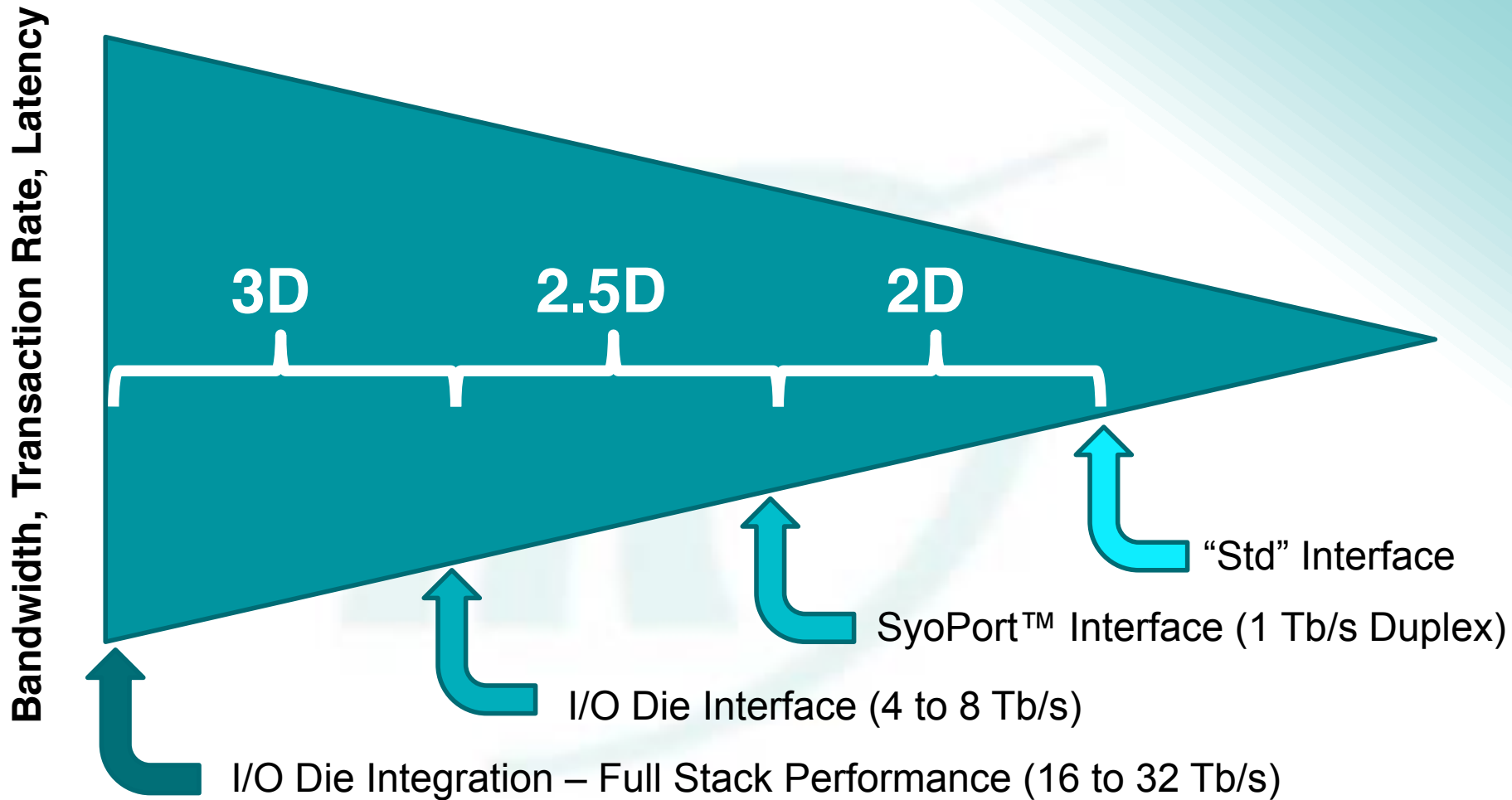
The Right I/O for Each Market

DiRAM4
Launches
with
0.7 V CMOS I/O
2.5D Si or Organic

- Low Power
- High Performance



Performance Choices





Tezzaron
SEMICONDUCTOR



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